

2SJ587

Silicon P Channel MOS FET
High Speed Switching

HITACHI

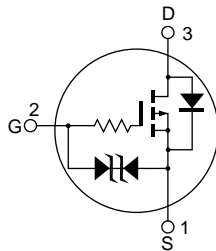
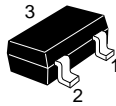
ADE-208-801 (Z)
1st.Edition.
June 1999

Features

- Low on-resistance
 $R_{DS} = 8.5 \Omega$ typ. ($V_{GS} = -4 \text{ V}$, $I_D = -25 \text{ mA}$)
 $R_{DS} = 15$ typ. ($V_{GS} = -2.5 \text{ V}$, $I_D = -10 \text{ mA}$)
- 2.5 V gate drive device.
- Small package (SMPAK)

Outline

SMPAK



1. Source
2. Gate
3. Drain

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-20	V
Gate to source voltage	V_{GSS}	±10	V
Drain current	I_D	-50	mA
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-200	mA
Body-drain diode reverse drain current	I_{DR}	-50	mA
Channel dissipation	Pch ^{Note 2}	100	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

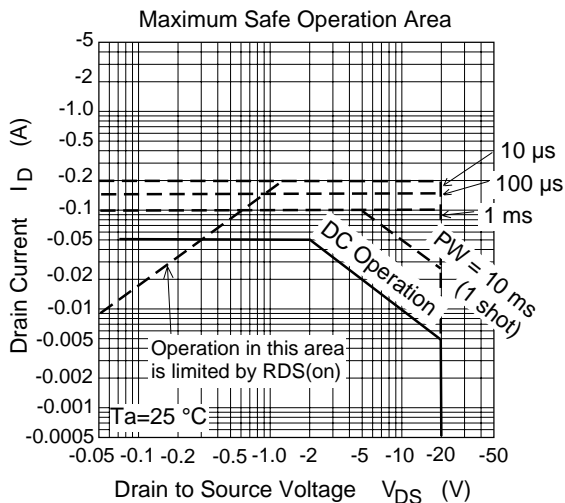
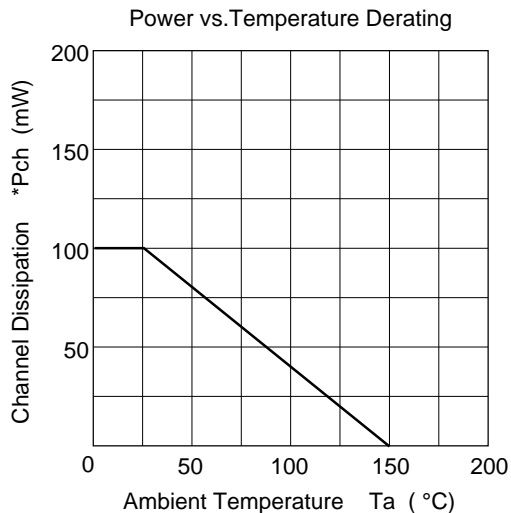
Note: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value on the alumina ceramic board (12.5x 20 x0.7 mm)

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±10	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±5	μA	$V_{GS} = \pm 8 V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -20 V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.8	—	-1.8	V	$I_D = -10 \mu A, V_{DS} = -5 V$
Static drain to source on state resistance	$R_{DS(on)}$	—	4.1	5.0	Ω	$I_D = -25 mA, V_{GS} = -4 V$ ^{Note 3}
	$R_{DS(on)}$	—	6.0	8.5	Ω	$I_D = -10 mA, V_{GS} = -2.5 V$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	32.5	50	—	mS	$I_D = -25 mA, V_{DS} = -10 V$ ^{Note 3}
Input capacitance	Ciss	—	13	—	pF	$V_{DS} = -10 V$
Output capacitance	Coss	—	10	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	1.8	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	22	—	ns	$I_D = -25 mA, V_{GS} = -4 V$
Rise time	t_r	—	48	—	ns	$R_L = 400 \Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	
Fall time	t_f	—	60	—	ns	

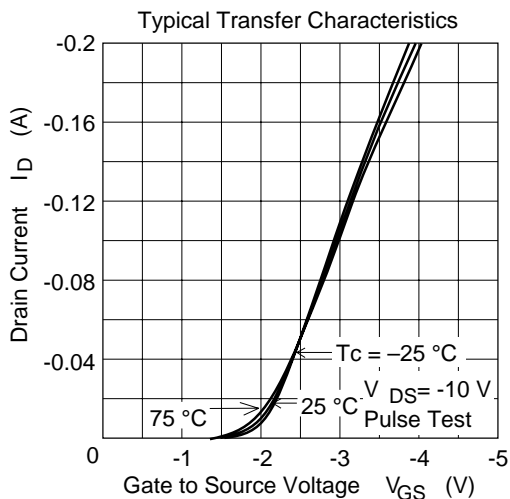
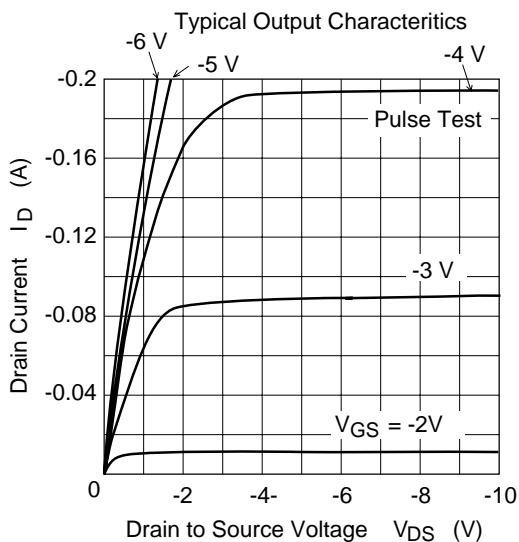
Note: 3. Pulse test
 4. Marking is DP

Main Characteristics

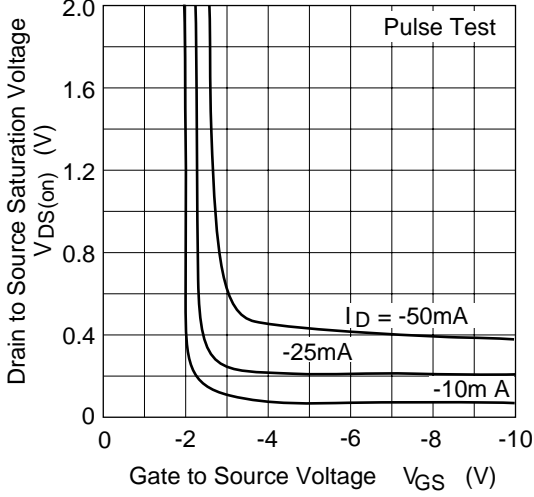


*Value on the alumina ceramic board.(12.5x20x0.7mm)

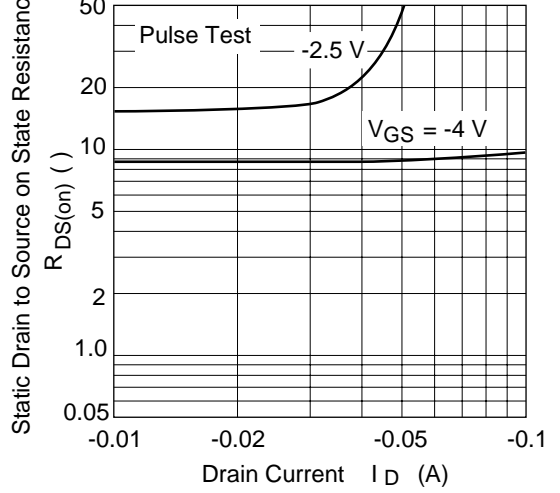
Value on the alumina ceramic board.(12.5x20x0.7mm)



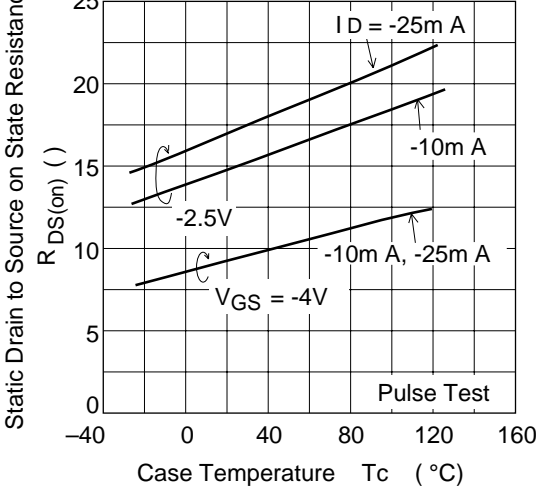
Drain to Source Saturation Voltage vs. Gate to Source Voltage



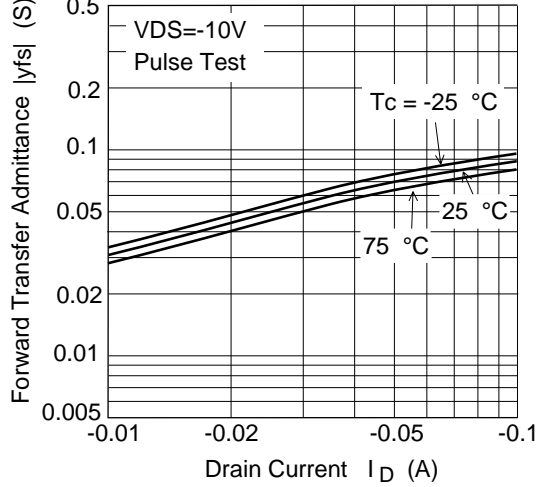
Static Drain to Source on State Resistance vs. Drain Current

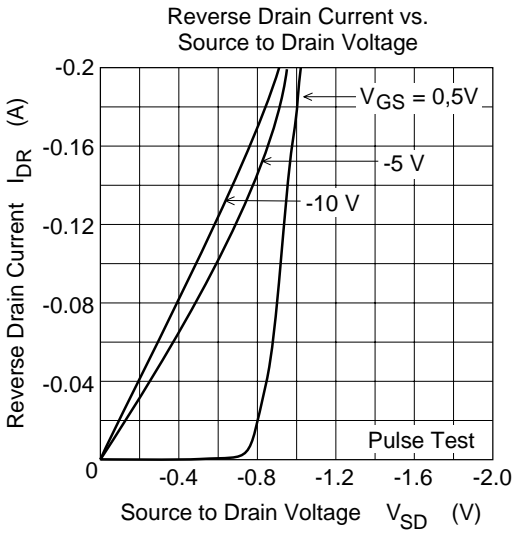
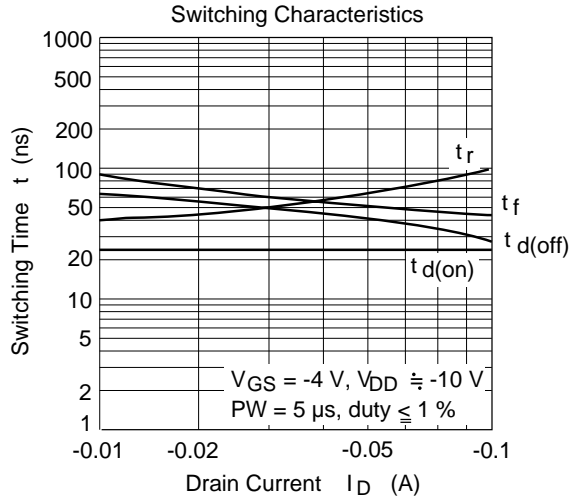
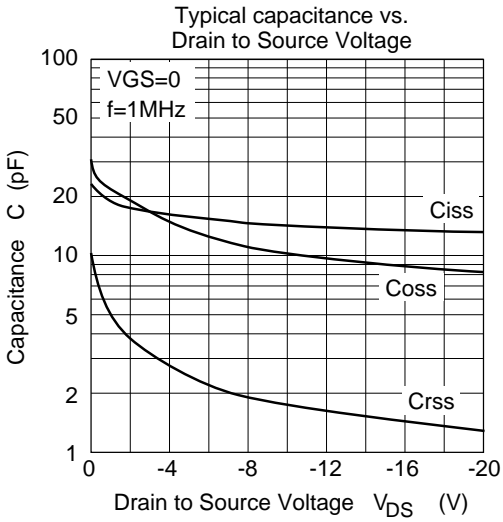


Static Drain to Source on State Resistance vs. Temperature

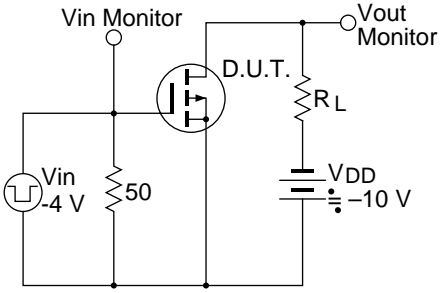


Forward Transfer Admittance vs. Drain Current

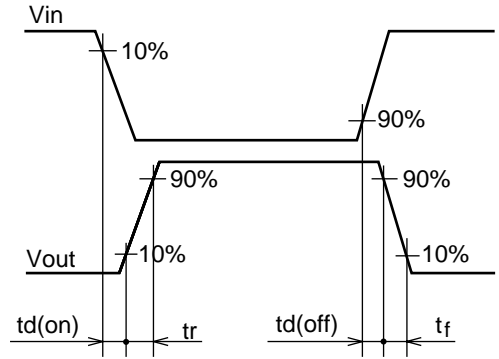




Switching Time Test Circuit

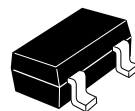
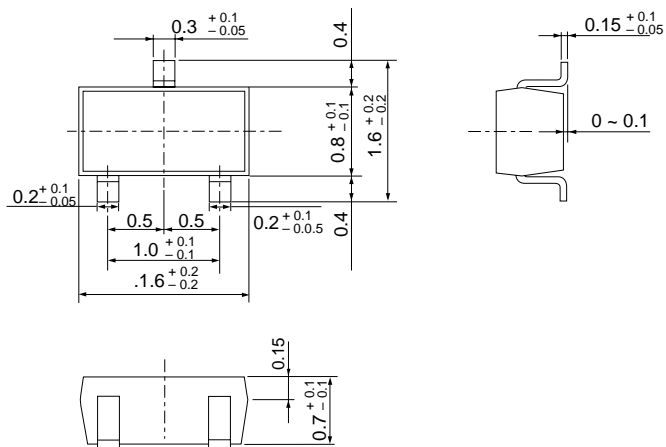


Waveforms



Package Dimensions

Unit: mm



Hitachi Code	SMPAK
EIAJ	-
JEDEC	-

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